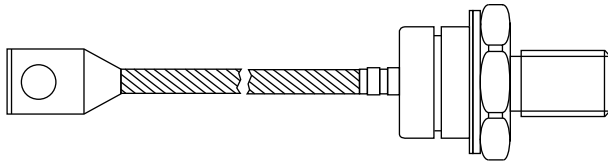




Standard Recovery Diodes (Stud Version), 200 A



DO-205AC (DO-30)

FEATURES

- Wide current range
- High voltage ratings up to 2400 V
- High surge current capabilities
- Stud cathode and stud anode version
- Standard JEDEC® types
- Compression bonded encapsulations
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



PRODUCT SUMMARY	
$I_{F(AV)}$	200 A
Package	DO-205AC (DO-30)
Circuit configuration	Single diode

TYPICAL APPLICATIONS

- Converters
- Power supplies
- Machine tool controls
- High power drives
- Medium traction applications

MAJOR RATINGS AND CHARACTERISTICS				
PARAMETER	TEST CONDITIONS	VS-SD200N/R		UNITS
		1600 to 2000	2400	
$I_{F(AV)}$		200		A
	T_C	110		°C
$I_{F(RMS)}$		314		A
I_{FSM}	50 Hz	4700		
	60 Hz	4920		
I^2t	50 Hz	110		kA ² s
	60 Hz	101		
V_{RRM}	Range	1600 to 2000	2400	V
T_J		-40 to 180	150	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V_{RRM} : MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V_{RSM} : MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-SD200N/R	16	1600	1700	15
	20	2000	2100	
	24	2400	2500	



FORWARD CONDUCTION					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average forward current at case temperature	I _{F(AV)}	180° conduction, half sine wave		200	A
				110	°C
Maximum average forward current at case temperature				220	A
				100	°C
Maximum RMS forward current	I _{F(RMS)}	DC at 95 °C case temperature		314	A
Maximum peak, one-cycle forward, non-repetitive surge current	I _{FSM}	t = 10 ms	No voltage reapplied	4700	
		t = 8.3 ms	No voltage reapplied	4920	
		t = 10 ms	100 % V _{RRM} reapplied	3950	
		t = 8.3 ms	100 % V _{RRM} reapplied	4140	
Maximum I ² t for fusing	I ² t	t = 10 ms	No voltage reapplied	110	kA ² s
		t = 8.3 ms	No voltage reapplied	101	
		t = 10 ms	100 % V _{RRM} reapplied	78	
		t = 8.3 ms	100 % V _{RRM} reapplied	71	
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10 ms, no voltage reapplied		1100	kA ² √s
Low level value of threshold voltage	V _{F(TO)1}	(16.7 % × π × I _{F(AV)} < I < π × I _{F(AV)}), T _J = T _J maximum		0.90	V
High level value of threshold voltage	V _{F(TO)2}	(I > π × I _{F(AV)}), T _J = T _J maximum		1.00	
Low level value of forward slope resistance	r _{f1}	(16.7 % × π × I _{F(AV)} < I < π × I _{F(AV)}), T _J = T _J maximum		0.79	mΩ
High level value of forward slope resistance	r _{f2}	(I > π × I _{F(AV)}), T _J = T _J maximum		0.64	
Maximum forward voltage drop	V _{FM}	I _{pk} = 630 A, T _J = T _J maximum, t _p = 10 ms sinusoidal wave		1.40	V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	SD200N/R		UNITS
			1600 to 2000	2400	
Maximum junction operating temperature range	T _J		-40 to 180	-40 to 150	°C
Maximum storage temperature range	T _{Stg}		- 55 to 200		
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.23		K/W
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased	0.08		
Maximum allowed mounting torque ± 10 %		Not-lubricated threads	14		Nm
Approximate weight			120		g
Case style		See dimensions (link at the end of datasheet)	DO-205AC (DO-30)		



ΔR_{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.041	0.030	$T_J = T_J$ maximum	K/W
120°	0.049	0.051		
90°	0.063	0.068		
60°	0.093	0.096		
30°	0.156	0.157		

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

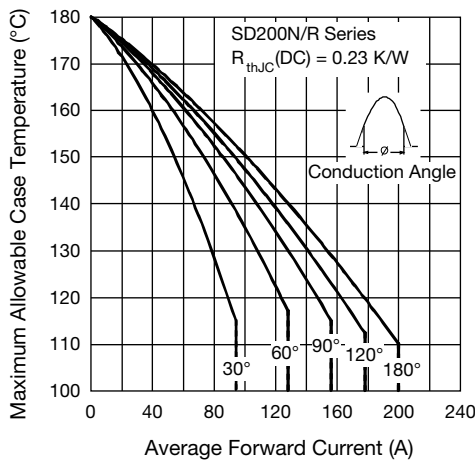


Fig. 1 - Current Ratings Characteristics

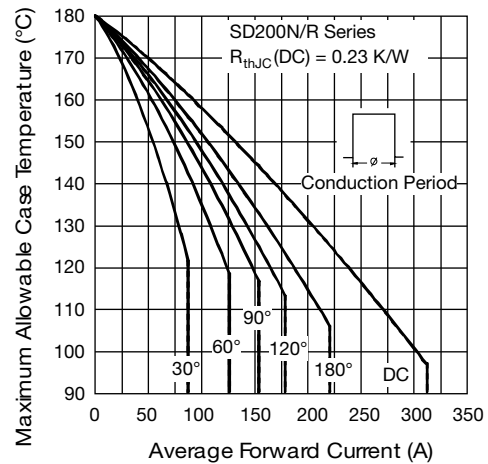


Fig. 2 - Current Ratings Characteristics

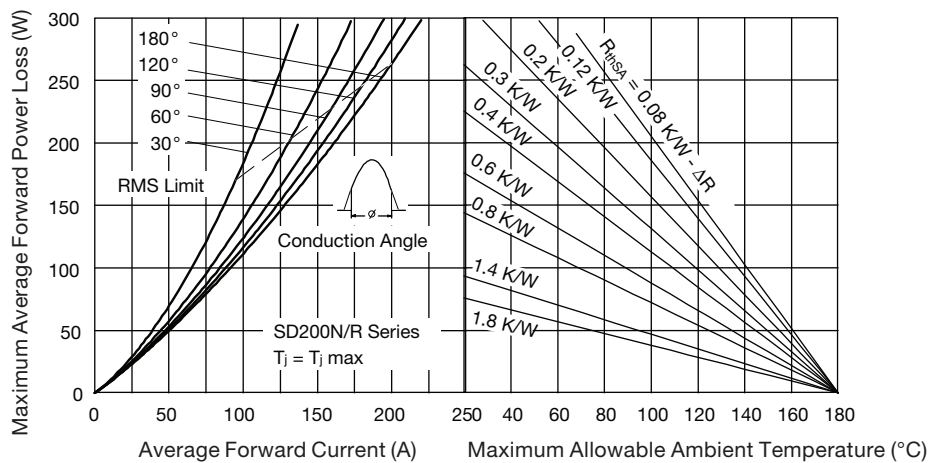


Fig. 3 - Forward Power Loss Characteristics

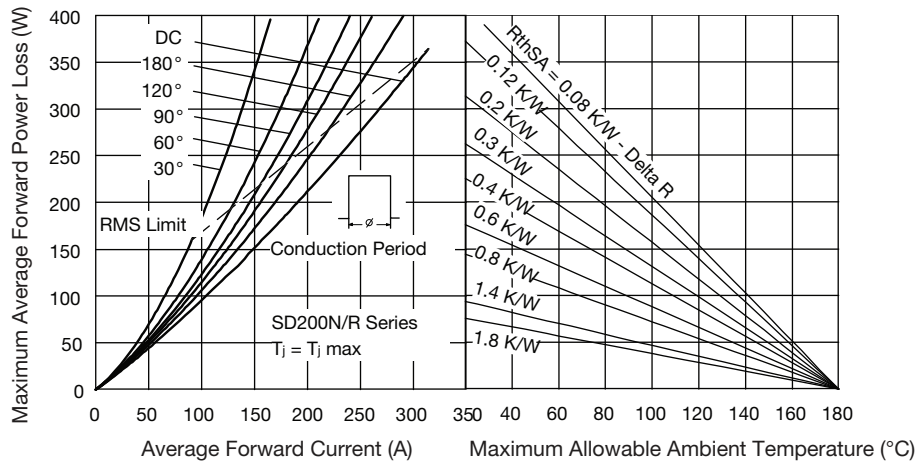


Fig. 4 - Forward Power Loss Characteristics

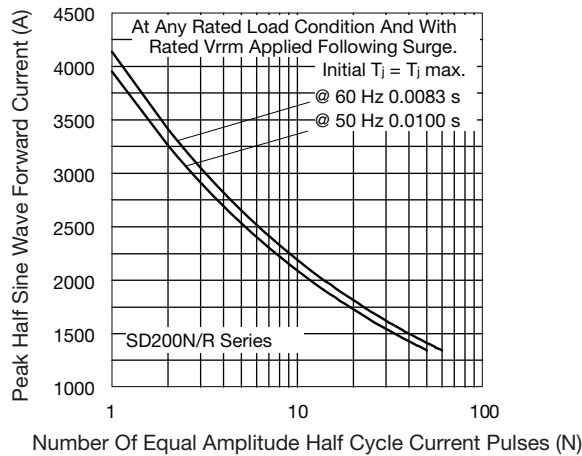


Fig. 5 - Maximum Non-Repetitive Surge Current

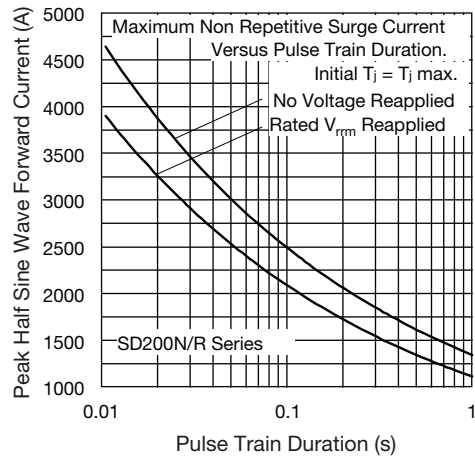


Fig. 6 - Maximum Non-Repetitive Surge Current

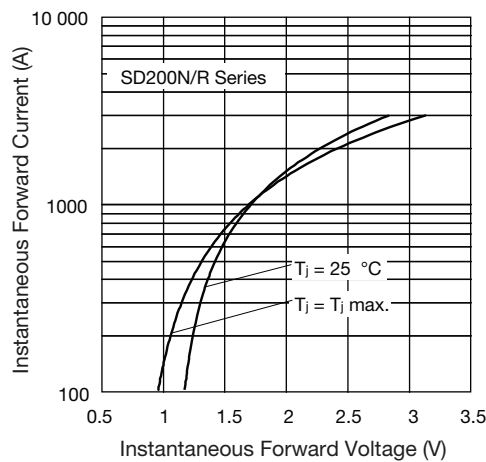


Fig. 7 - Forward Voltage Drop Characteristics

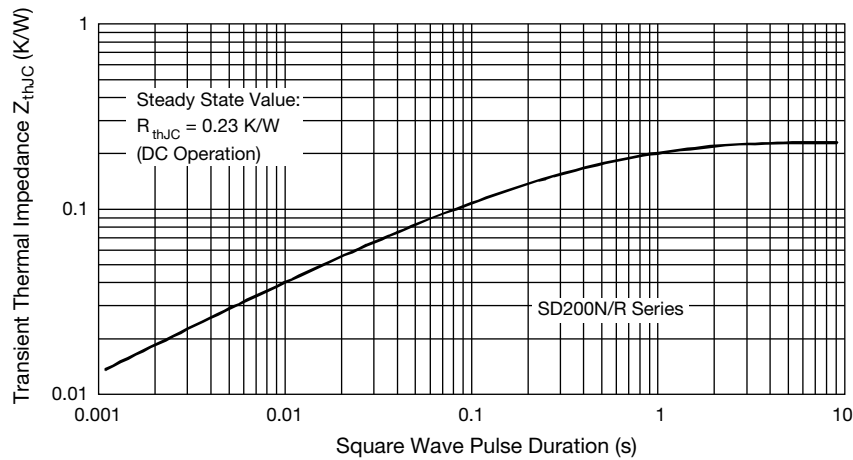


Fig. 8 - Thermal Impedance Z_{thJC} Characteristic

ORDERING INFORMATION TABLE

Device code	VS-	SD	20	0	N	24	P	C
	①	②	③	④	⑤	⑥	⑦	⑧

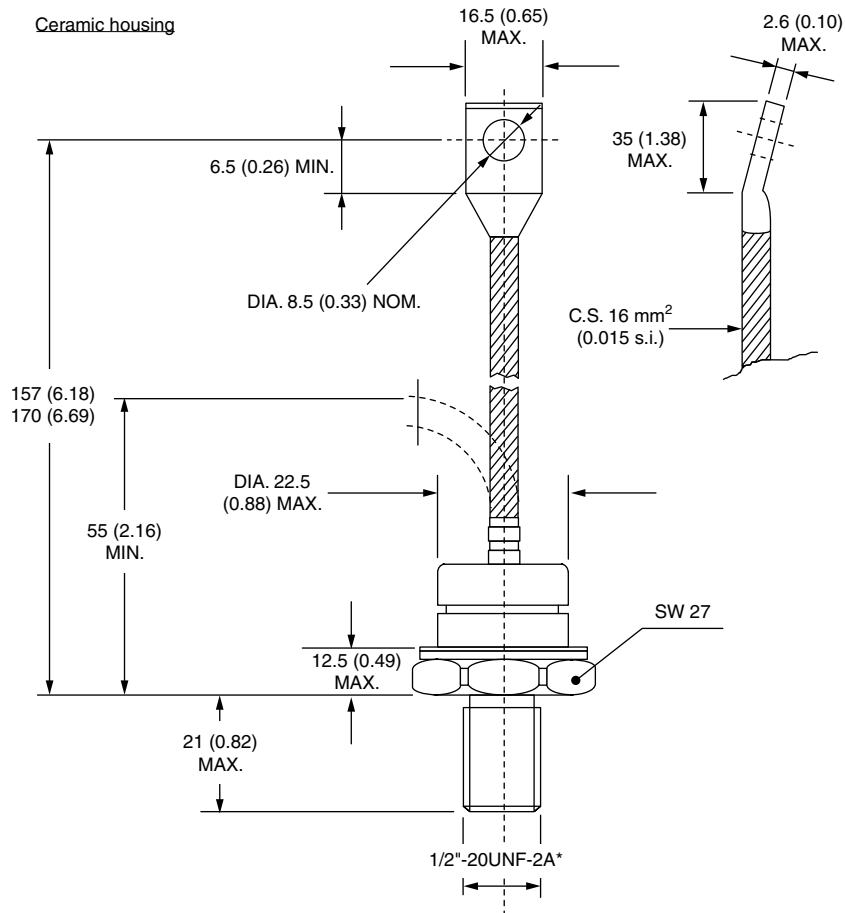
- 1** - Vishay Semiconductors product
- 2** - Diode
- 3** - Essential part number
- 4** - 0 = Standard recovery
- 5** -
 - N = Stud normal polarity (cathode to stud)
 - R = Stud reverse polarity (anode to stud)
- 6** - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- 7** -
 - P = Stud base DO-205AC (DO-30) 1/2" 20UNF-2A
 - M = Stud base DO-205AC (DO-30) M12 x 1.75
- 8** - C = Ceramic housing

For metric device M12 x 1.75 contact factory

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95302

DO-205AC (DO-30)

DIMENSIONS in millimeters (inches)



*For metric device: M12 x 1.75
contact factory



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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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